

0912GN-50LE/LEL/LEP

Datasheets

E-Series GaN Transistor Driver



**Microsemi Corporate Headquarters**

One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113

Outside the USA: +1 (949) 380-6100

Fax: +1 (949) 215-4996

Email: sales.support@microsemi.com

www.microsemi.com

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Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 was published in March 2017. It was the first publication of this document.

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2 Product Overview

The 0912GN-50LE/LEL/LEP device provides the following key features:

- 960 MHz–1215 MHz, 50 W pulsed output power, 32 μ s–2%, and MIDS pulsing
- Common-source, class-AB, 50 V bias voltage
- >60% efficiency across the frequency band under MIDS signal
- Extremely compact size
- 15.9 dB typical power gain
- 0.3 dB typical excellent gain flatness
- IFF, Mode-S, DME, TACAN, TCAS, and avionics secondary radars
- All-gold metallization and eutectic die attach for highest reliability
- 50 Ω IN/OUT lumped element, very small footprint, plug-and-play pallets available
- Export classification: EAR-99

The following illustrations show the case outlines of the 0912GN-50E/EL/EP device.

Figure 1 55-QQ Case Outline



Figure 2 55-QQP Case Outline

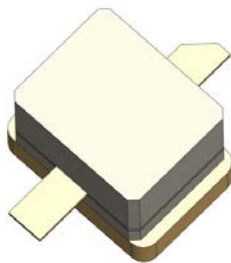
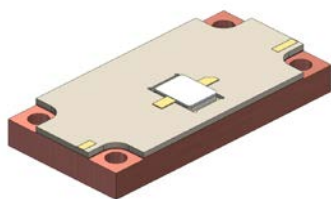


Figure 3 Pallet Outline



3 Electrical Specifications

This section details the electrical specifications of the of the 0912GN-50LE/LEL/LEP device.

3.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the 0912GN-50LE/LEL/LEP device.

Table 1 Absolute Maximum Ratings

Rating	Parameter	Value	Units
Maximum power dissipation	Device dissipation at 25 °C	100	W
Maximum voltage and current	Drain-source voltage (V_{DSS})	150	V
	Gate-source voltage (V_{GS})	-8 to 0	V
Maximum temperatures	Storage temperature (T_{STG})	-55 to 125	°C
	Operating junction temperature	200	°C

3.2 Electrical Characteristics

The following table shows the typical electrical characteristics of the 0912GN-50LE/LEL/LEP device at 25 °C.

Table 2 Electrical Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
P_{OUT}	Output power	$P_{IN} = 1.5$ W, Freq = 960 MHz, 1090 MHz, 1215 MHz	50	58		W
G_P	Power gain	$P_{IN} = 1.5$ W, Freq = 960 MHz, 1090 MHz, 1215 MHz	15.2	15.9		dB
η_D	Drain efficiency	$P_{IN} = 1.5$ W, Freq = 960 MHz, 1090 MHz, 1215 MHz	58	63		%
D_r	Droop	$P_{IN} = 1.5$ W, Freq = 960 MHz, 1090 MHz, 1215 MHz		0.4	0.7	dB
VSWR-T	Load mismatch tolerance	$P_{OUT} = 50$ W, Freq = 1090 MHz, 32 μ s – 2%			5:1	

Bias Condition: $V_{DD} = 50$ V, $I_{DQ} = 30$ mA constant current ($V_{GS} = -2.0$ V to -4.5 V typical)

3.3 Functional Characteristics

The following table shows the typical functional characteristics of the 0912GN-50LE/LEL/LEP device at 25 °C.

Table 3 Functional Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
$I_{D(off)}$	Drain leakage current	$V_{GS} = -8$ V, $V_D = 150$ V			4	mA
$I_{G(off)}$	Gate leakage current	$V_{GS} = -8$ V, $V_D = 0$ V			0.5	mA

3.4 Typical Broadband Performance Data

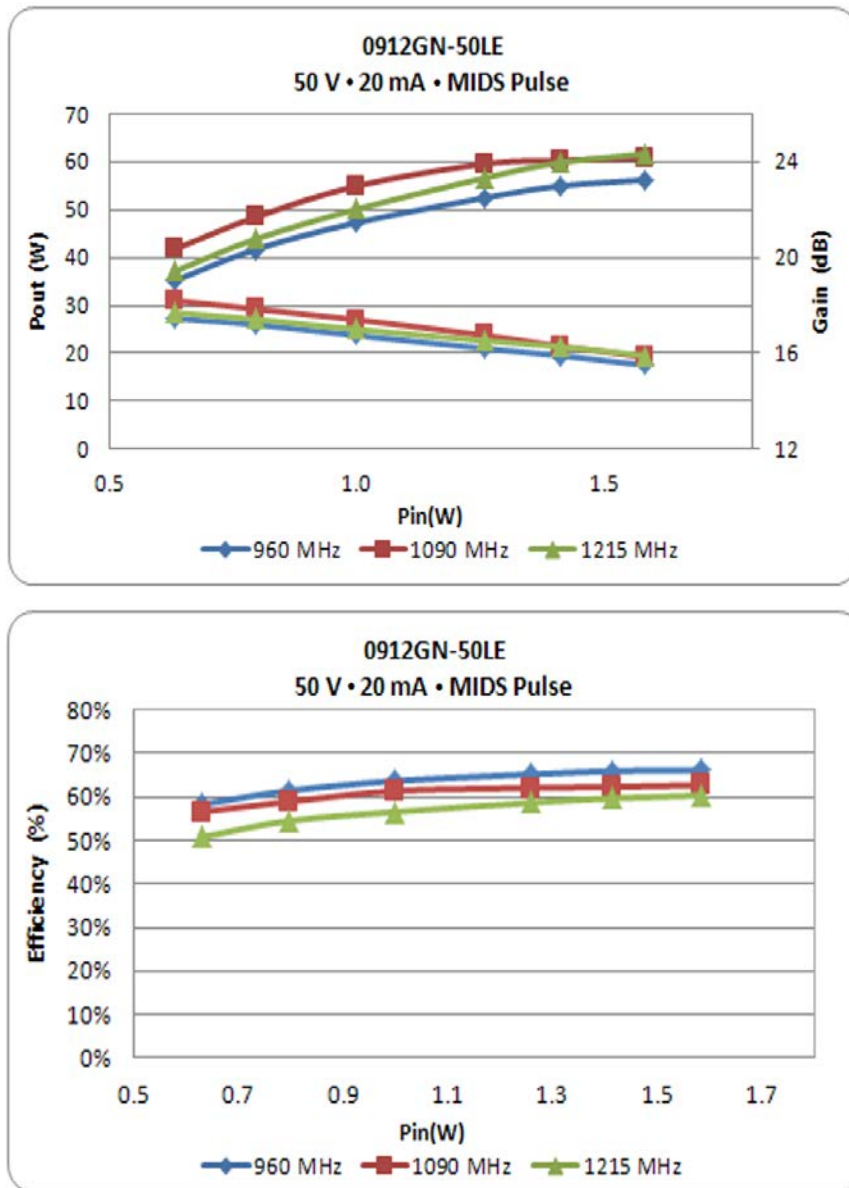
The following table shows the typical broadband performance data of the 0912GN-50LE/LEL/LEP device under MIDS pulsing (6.4 μs on/13 μs off, burst of 256 pulses, and duty cycle of 21%).

Table 4 Typical Broadband Performance Data (MIDS Pulsing)

Freq (MHz)	P _{IN} (W)	P _{OUT} (W)	I _D (A)	η _D at Pulse 1 (%)	Gain (dB)	Droop at Pulse 256 (dB)
960	1.6	57	0.380	66	15.6	0.30
1090	1.6	61	0.427	63	15.8	0.30
1215	1.6	62	0.449	30	15.9	0.45

The following graphs show the typical broadband performance of the 0912GN-50LE/LEL/LEP device.

Figure 4 Typical Broadband Performance Data Graphs



The following table shows the typical broadband performance data of the 0912GN-50LE/LEL/LEP device at 32 μ s, where DF = 2%.

Table 5 Typical Broadband Performance Data (32 μ s)

Freq (MHz)	P _{IN} (W)	P _{OUT} (W)	I _D (A)	RL (dB)	Gain (dB)	Droop (dB)
960	1.6	58	0.039	-12	15.65	0.05
1090	1.6	62	0.044	-7	15.90	0.05
1215	1.6	63	0.046	-5	15.97	0.05

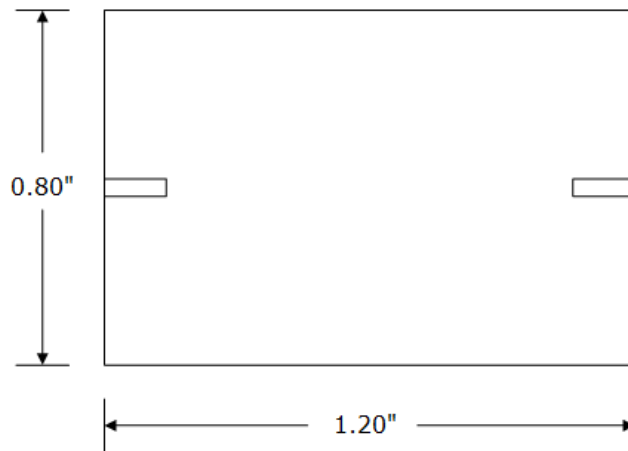
4 Package Information

This section details the package information of the 0912GN-50LE/LEL/LEP device.

4.1 Transistor Test Fixture Dimensions

The following illustration shows the transistor test fixture dimensions of the 0912GN-50LE/LEL/LEP device. The dimensions are in inches. Contact your Microsemi sales representative for test fixtures.

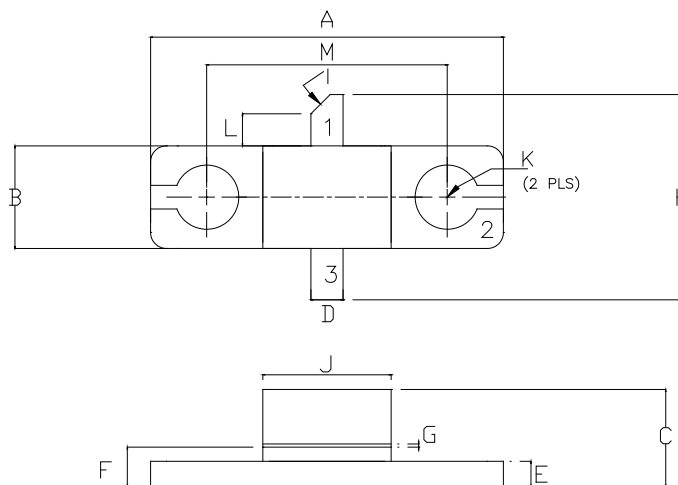
Figure 5 Transistor Test Fixture Dimensions



4.2 55-QQ Package

The following drawing shows the 55-QQ package outline of the 0912GN-50LE/LEL/LEP device. PIN 1 is the drain, PIN 2 is the source, and PIN 3 is the gate.

Figure 6 55-QQ Package Outline



The following table shows the 55-QQ dimensions of the 0912GN-50LE/LEL/LEP device, and it corresponds to [Figure 6](#).

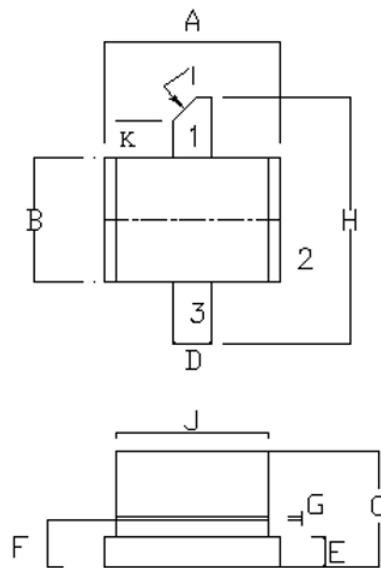
Table 6 55-QQ Package Dimensions

Dimension	Millimeters	Tol (mm)	Inches	Tol (in.)
A	13.970	0.250	0.550	0.010
B	4.570	0.250	0.160	0.010
C	3.860	0.330	0.152	0.013
D	1.270	0.130	0.050	0.005
E	1.020	0.130	0.040	0.005
F	1.700	0.130	0.067	0.005
G	0.130	0.025	0.005	0.001
H	8.130	0.250	0.320	0.010
I	45°	5°	45°	5°
J	5.080	0.250	0.200	0.010
K	2.54 DIA	0.130	0.100 DIA	0.005
L	1.270	0.130	0.050	0.005
M	9.530	0.130	0.375	0.005

4.3 55-QQP Package

The following illustration shows the 55-QQP package outline of the 0912GN-50LE/LEL/LEP device. PIN 1 is the drain, PIN 2 is the source, and PIN 3 is the gate.

Figure 7 55-QQP Package Outline



The following table shows the 55-QQP dimensions of the 0912GN-50LE/LEL/LEP device, and it corresponds to [Figure 7](#).

Table 7 55-QQP Package Dimensions

Dimension	Millimeters	Tol (mm)	Inches	Tol (in.)
A	5.840	0.250	0.230	0.010
B	4.060	0.250	0.160	0.010
C	3.170	0.050	0.125	0.002
D	1.270	0.130	0.050	0.005
E	1.020	0.130	0.040	0.005
F	1.570	0.130	0.062	0.005
G	0.130	0.020	0.005	0.001
H	8.120	0.250	0.320	0.010
I	45°	5°	45°	5°
J	5.080	0.250	0.200	0.010
K	1.400	0.130	0.055	0.005

4.4 Pallet Package

The following illustration shows the pallet outline and the overall pallet dimensions of the 0912GN-50LE/LEL/LEP device. It is 1.200 inches long, 0.600 inches wide, and 0.150 inches high.

Figure 8 Pallet Package Outline